

Supporting information for: Charge transfer and electronic doping in nitrogen-doped graphene

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In Fig. 1 we display typical EDC from which the electronic doping level was measured.

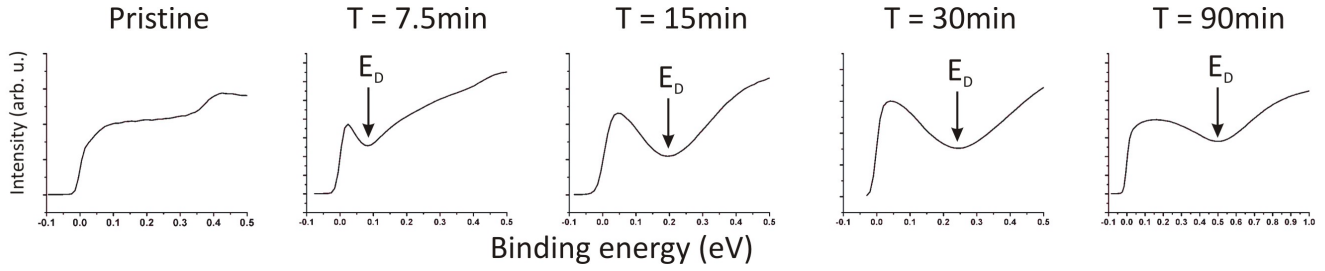


FIG. 1: Typical EDCs for the different samples from which the electronic doping level was extracted.

In Fig. 2 we report the concentration of doping sites, measured by counting the doping sites in STM images, as a function of the exposure time of the graphene samples to nitrogen flux. The quasi linear relation shows that the doping level is well controlled by controlling the exposure time.

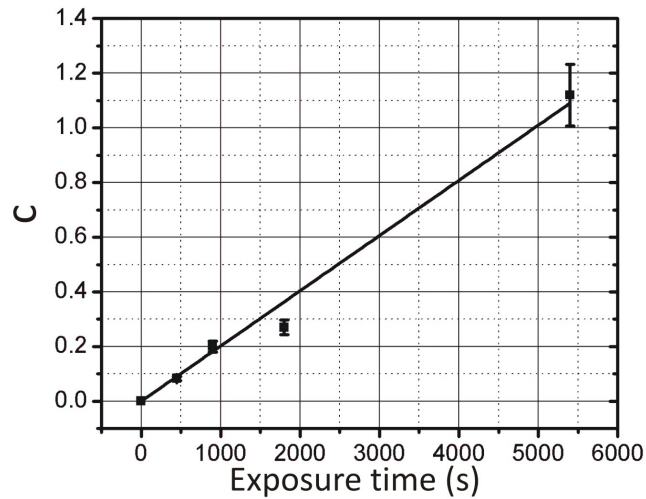


FIG. 2: Doping level (atomic nitrogen concentration; in percent) as a function of the time of exposure of the graphene samples to the radical nitrogen flux.